

# 405nm Laser Diode

## ■ Features

- Output Power: 100mW (CW)
- Efficient Quantum Well Structure
- Standard TO-18 Package



## ■ Absolute Maximum Ratings

(Tc=25°C)

Item	Symbol	Absolute Maximum Ratings	Unit
Optical Output Power	Po	100	mW
LD Reverse Voltage	Vr (LD)	5	V
PD Reverse Voltage	Vr (PD)	-	V
Storage Temperature	Tstg	-40~85	°C
Operating Case Temperature	Tc	-10~70	°C

## ■ Initial Electrical/Optical Characteristics

(Tc=25°C)

Item	Condition	Symbol	Typ.	Unit
Optical Output	CW	Po	100	mW
Peak Wavelength*	Po=100mW	λp	405	nm
Threshold Current	CW	Ith	≤0.035	A
Operating Current	Po=100mW	Iop	≤0.12	A
Slope Efficiency	CW	η	≥1.3	W/A
Operating Voltage	Po=100mW	Vop	≤4.6	V
FWHM Beam Divergence	Po=100mW	θ //	≤9	deg.
		θ ⊥	≤20	deg.
Wavelength	Po=100mW		0.3	nm/°C
Temperature Coefficient				
Polarization	Po=100mW		TE	

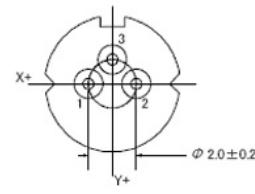
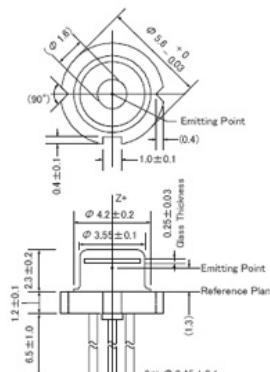
\* Measuring specifications.

All figures in this specification are measured by CNI's method and may contain measurement deviations

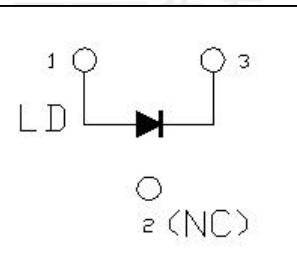
The above specifications are for reference purpose only and subjected to change without prior notice.

## Outline Dimension

### TO-18 Package



## Pin Connection



Changchun New Industries Optoelectronics Tech. Co., Ltd  
<http://www.cnilaser.com>

## ◆ CONTACT

No.668, Chuangxin Road, High-tech zone,  
Changchun 130012, China  
 Phone: 0086-431-85603799  
 Fax: 0086-431-87020258